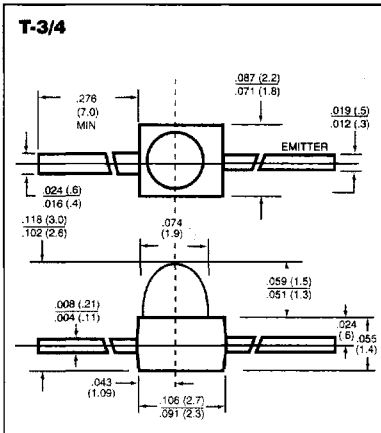


Part Number	Emission Angle	Radiant Intensity		V_e/I_e	I_R/V_R	Notes
(Emitters) 1/2 Power		min	max	units	(V)/(mA)	(μ A)/(V)
940 nm GaAs						
QEB363	$\pm 12^\circ$	8	—	mW/sr	1.6/20	100/5 1,3
880 nm AlGaAs						
QEB373	$\pm 12^\circ$	16	—	mW/sr	1.7/20	100/5 1



Part Number	Reception Angle	Sensitivity		BV_{CE}	I_{CEO}/V_{CE}	Notes
(Sensors) 1/2		min	max	units	(mV)	(nA)/(V)
Phototransistor						
QSB363	$\pm 12^\circ$	0.7	—	mA	30	100/10 2

Notes

1. I_e @ $I_F = 100$ mA pulsed
2. On-State Collector Current @ $E_e = 0.5$ mW/cm² (AlGaAs), $V_{CE} = 5$ V
3. Reverse Polarity

Maximum Ratings Table E (Applies to all components on this page.)

Storage Temperature	-40 to +85° C
Operating Temperature	-40 to +85° C
Soldering:	
Lead Temperature (Iron)	240° C for 5 s
Lead Temperature (Flow)	260° C for 10 s
QEB	
Continuous Forward Current	50 mA
Reverse Voltage	5.0 V
Power Dissipation	100 mW
Derate linearly at 1.33 mW/° C above 25° C	
QSB	
Collector-Emitter Breakdown Voltage	30 mA
Emitter-Collector Breakdown Voltage	5.0 V
Power Dissipation	100 mW
Derate linearly at 1.33 mW/° C above 25° C	